

# Xiao Yu

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Aggressive EOT Scaling of Ge pMOSFETs With $\text{HfO}_2/\text{AlO}_x/\text{GeO}_x$ Gate-Stacks Fabricated by Ozone Postoxidation. IEEE Electron Device Letters, 2016, 37, 831-834.		50
2	Impact of Plasma Postoxidation Temperature on the Electrical Properties of $\text{Al}_2\text{O}_3/\text{GeO}_x/\text{Ge}$ pMOSFETs and nMOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 416-422.	3.0	34
3	$\text{HfO}_2$ - $\text{ZrO}_2$ Superlattice Ferroelectric Capacitor With Improved Endurance Performance and Higher Fatigue Recovery Capability. IEEE Electron Device Letters, 2022, 43, 216-219.	3.9	33
4	Ultra fast (<1 ns) electrical characterization of self-heating effect and its impact on hot carrier injection in 14nm FinFETs. , 2017, , .		30
5	Impact of Channel Orientation on Electrical Properties of Ge p- and n-MOSFETs With 1-nm EOT $\text{Al}_2\text{O}_3/\text{GeO}_x/\text{Ge}$ Gate-Stacks Fabricated by Plasma Postoxidation. IEEE Transactions on Electron Devices, 2014, 61, 3668-3675.	3.0	24
6	Impact of back interface passivation on electrical properties of ultrathin-body Germanium-on-insulator (GeOI) MOSFETs. Microelectronic Engineering, 2015, 147, 196-200.	2.4	16
7	Characterization of ultrathin-body Germanium-on-insulator (GeOI) structures and MOSFETs on flipped Smart-Cut $\text{\AA}$ , GeOI substrates. Solid-State Electronics, 2016, 115, 120-125.	1.4	15
8	Real-Time Polarization Switch Characterization of $\text{HfZrO}_4$ for Negative Capacitance Field-Effect Transistor Applications. IEEE Electron Device Letters, 2018, 39, 1469-1472.	3.9	15
9	Investigation of Self-Heating Effect on Ballistic Transport Characterization for Si FinFETs Featuring Ultrafast Pulsed IV Technique. IEEE Transactions on Electron Devices, 2017, 64, 909-915.	3.0	14
10	Analog Synapses Based on Nonvolatile FETs With Amorphous $\text{ZrO}_2$ Dielectric for Spiking Neural Network Applications. IEEE Transactions on Electron Devices, 2022, 69, 1028-1033.	3.0	12
11	Impact of Postdeposition Annealing Ambient on the Mobility of Ge nMOSFETs With 1-nm EOT $\text{Al}_2\text{O}_3/\text{GeO}_x/\text{Ge}$ Gate-Stacks. IEEE Transactions on Electron Devices, 2016, 63, 558-564.	3.0	11
12	A Fast $V_{th}$ Measurement (FVM) Technique for NBTI Behavior Characterization. IEEE Electron Device Letters, 2018, 39, 172-175.	3.9	11
13	Evaluation of Mobility Degradation Factors and Performance Improvement of Ultrathin-Body Germanium-on-Insulator MOSFETs by GOI Thinning Using Plasma Oxidation. IEEE Transactions on Electron Devices, 2017, 64, 1418-1425.	3.0	10
14	Back-Gate Modulation in UTB GeOI pMOSFETs With Advanced Substrate Fabrication Technique. IEEE Transactions on Electron Devices, 2018, 65, 895-900.	3.0	8
15	Ultra-Fast (ns-Scale) Characterization of NBTI Behaviors in Si pFinFETs. IEEE Journal of the Electron Devices Society, 2020, 8, 577-583.	2.1	8
16	Experimental Investigation of Ballistic Carrier Transport for Sub-100-nm Ge n-MOSFETs. IEEE Electron Device Letters, 2017, 38, 434-437.	3.9	7
17	Ultrafast pulse characterization of hot carrier injection effects on ballistic carrier transport for sub-100 nm MOSFETs. , 2017, , .		6
18	Compact models for influential nodes identification problem in directed networks. Chaos, 2020, 30, 053126.	2.5	6

#	ARTICLE	IF	CITATIONS
19	Electrical Properties of Ge pMOSFETs With Ultrathin EOT HfO <sub>2</sub> /AlO <sub>x</sub> /GeO <sub>x</sub> Gate-Stacks and NiGe Metal Source/Drain. IEEE Transactions on Electron Devices, 2017, 64, 4831-4837.		5
20	Ge N-Channel MOSFETs with ZrO <sub>2</sub> Dielectric Achieving Improved Mobility. Nanoscale Research Letters, 2021, 16, 125.	5.7	5
21	Ferroelectric-Like Non-Volatile FET With Amorphous Gate Insulator for Supervised Learning Applications. IEEE Journal of the Electron Devices Society, 2021, 9, 1145-1150.	2.1	4
22	Quantitative Characterization of Fast-Trap Behaviors in Al <sub>2</sub> O <sub>3</sub> /GeO <sub>x</sub> /Ge pMOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 2729-2735.	3.0	3
23	All-Optical Synapse With Directional Coupler Structure Based on Phase Change Material. IEEE Photonics Journal, 2021, 13, 1-6.	2.0	3
24	Effect of thickness scaling on the switching dynamics of ferroelectric HfO <sub>2</sub> /ZrO <sub>2</sub> capacitors. Ceramics International, 2022, 48, 28489-28495.	4.8	2
25	Direct-Bandgap Electroluminescence From Germanium With Subband Engineering Utilizing a Metal-Oxide-Semiconductor Structure. IEEE Transactions on Electron Devices, 2020, 67, 2016-2021.	3.0	1
26	Impact of post metallization annealing (PMA) on the electrical properties of Ge nMOSFETs with ZrO <sub>2</sub> dielectric. Solid-State Electronics, 2022, 190, 108240.	1.4	0